2SC1360, 2SC1360A

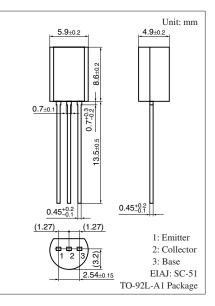
Silicon NPN epitaxial planar type

For intermediate frequency amplification of TV image

Features

- High transition frequency f_T
- \bullet Large collector power dissipation P_{C}

| Parameter | Symbol | Rating | Unit | |
|----------------------------|------------------|------------------|------|---|
| Collector-base voltage | 2SC1360 | V _{CBO} | 50 | V |
| (Emitter open) | 2SC1360A | | 60 | |
| Collector-emitter voltage | 2SC1360 | V _{CEO} | 45 | V |
| (Base open) | 2SC1360A | | 60 | |
| Emitter-base voltage (Col | V _{EBO} | 4 | V | |
| Collector current | I _C | 50 | mA | |
| Collector power dissipatio | P _C | 1 | W | |
| Junction temperature | Tj | 150 | °C | |
| Storage temperature | T _{stg} | -55 to +150 | °C | |



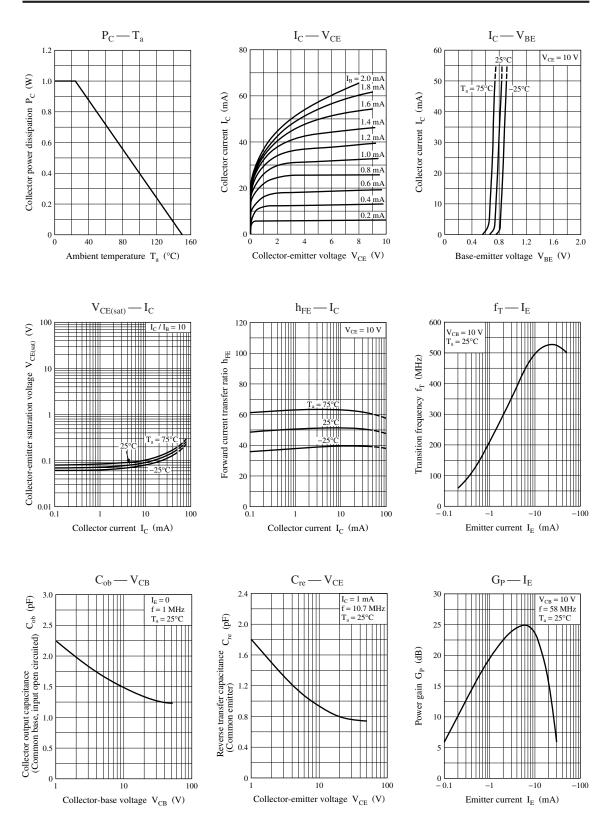
Absolute Maximum Ratings $T_a = 25^{\circ}C$

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

| Parameter | | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------|----------------------|--|-----|------|-----|------|
| Collector-base voltage | 2SC1360 | V _{CBO} | $I_{\rm C} = 100 \ \mu \text{A}, \ I_{\rm E} = 0$ | 50 | | | V |
| (Emitter open) | 2SC1360A | 1 | | 60 | | | |
| Collector-emitter voltage | 2SC1360 | V _{CEO} | $I_{\rm C} = 3 \text{ mA}, I_{\rm B} = 0$ | 45 | | | V |
| (Base open) | 2SC1360A |] | $I_{\rm C} = 1 {\rm mA}, I_{\rm B} = 0$ | 60 | | | |
| Emitter-base voltage (Collector open) | | V _{EBO} | $I_E = 100 \ \mu A, \ I_C = 0$ | 4 | | | V |
| Collector-base cutoff current (Emitter open) | | I _{CBO} | $V_{CB} = 20 V, I_E = 0$ | | | 100 | nA |
| Forward current transfer ratio | | h _{FE} | $V_{CE} = 10 \text{ V}, \text{ I}_{C} = 10 \text{ mA}$ | 20 | 50 | 100 | |
| Collector-emitter saturation voltage | | V _{CE(sat)} | $I_{\rm C} = 20 \text{ mA}, I_{\rm B} = 2 \text{ mA}$ | | | 0.4 | V |
| Transition frequency | 2SC1360 | f _T | $V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 100 \text{ MHz}$ | 300 | 500 | | MHz |
| | 2SC1360A | 1 | | 300 | | | |
| Reverse transfer capacitance | 2SC1360 | C _{re} | $V_{CB} = 10 \text{ V}, I_E = -1 \text{ mA}, f = 10.7 \text{ MHz}$ | | 0.96 | 1.5 | pF |
| (Common emitter) | 2SC1360A | 1 | | | | 1.5 | |
| Power gain | 2SC1360 | G _P | $V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 58 \text{ MHz}$ | 22 | 26 | 30 | dB |
| | 2SC1360A | 1 | | 22 | | 30 | |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Panasonic



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